P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I_D (A)[a]	Q_g (Typ.)
- 30	0.046 at V_{GS} = - 10 V	- 5.6	11.4 nC
	0.049 at V_{GS} = - 6 V	- 5	
	0.054 at V_{GS} = - 4.5 V	-4.5	

FEATURES

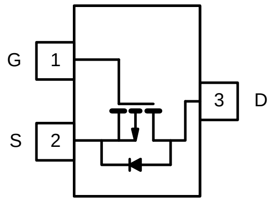
- TrenchFET® Power MOSFET
- 100 % R_g Tested

APPLICATIONS

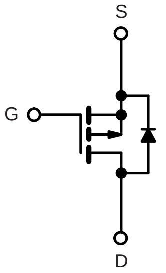
- For Mobile Computing
  - Load Switch
  - Notebook Adaptor Switch
  - DC/DC Converter

RoHS
COMPLIANT
HALOGEN
FREE

(SOT-23)
TO-236



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 5.6	A
	T_C = 70 °C		- 5.1	
	T_A = 25 °C		- 5.4[b,c]	
	T_A = 70 °C		- 4.3[b,c]	
Pulsed Drain Current (t = 100 µs)		I_{DM}	- 18	
Continous Source-Drain Diode Current	T_C = 25 °C	I_S	- 2.1	
	T_A = 25 °C		- 1[b,c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.5	W
	T_C = 70 °C		1.6	
	T_A = 25 °C		1.25[b,c]	
	T_A = 70 °C		0.8[b,c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b,d]	t ≤ 5 s	R_{thJA}	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

Notes:

a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 166 °C/W.

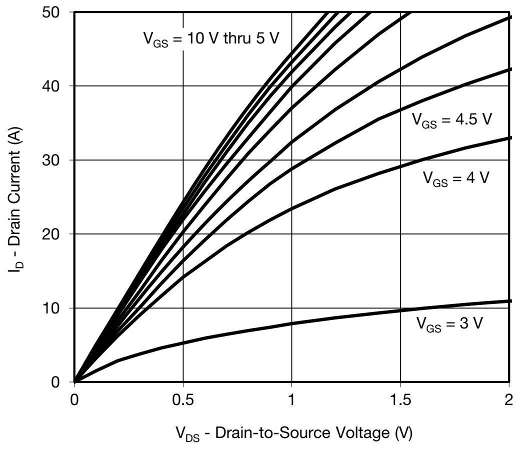
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 19		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = - 250 µA	- 0.5		- 2.0	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 30 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 30 V, V_{GS} = 0 V, T_J = 55 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ - 5 V, V_{GS} = - 10 V	- 2.5			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} =- 10 V, I_D = - 4.4 A		0.046	0.055	Ω
		V_{GS} =- 6 V, I_D = - 4 A		0.049	0.058	
		V_{GS} =- 4.5 V, I_D = - 3.6 A		0.054	0.063	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 3.4 A		18		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 15 V, V_{GS} = 0 V, f = 1 MHz		1295		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			130		
Total Gate Charge	Q_g	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 5.4 A		24	36	nC
		V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_D = - 5.4 A		11.4	17	
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			3.8		
Gate Resistance	R_g	f = 1 MHz	1.5	7.7	15.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 3.5 Ω I_D ≅ - 4.3 A, V_{GEN} = - 10 V, R_g = 1 Ω		13	20	ns
Rise Time	t_r			4	8	
Turn-Off Delay Time	$t_{d(off)}$			38	57	
Fall Time	t_f			6	12	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 3.5 Ω I_D ≅ - 4.3 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		28	42	
Rise Time	t_r			16	24	
Turn-Off Delay Time	$t_{d(off)}$			30	45	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 2.1	A
Pulse Diode Forward Current (t = 100 µs)	I_{SM}				- 80	
Body Diode Voltage	V_{SD}	I_S = - 4.3 A, V_{GS} = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 4.3 A, dI/dt = 100 A/µs, T_J = 25 °C		15	23	ns
Body Diode Reverse Recovery Charge	Q_{rr}			7	14	nC
Reverse Recovery Fall Time	t_a			8		ns
Reverse Recovery Rise Time	t_b			7		

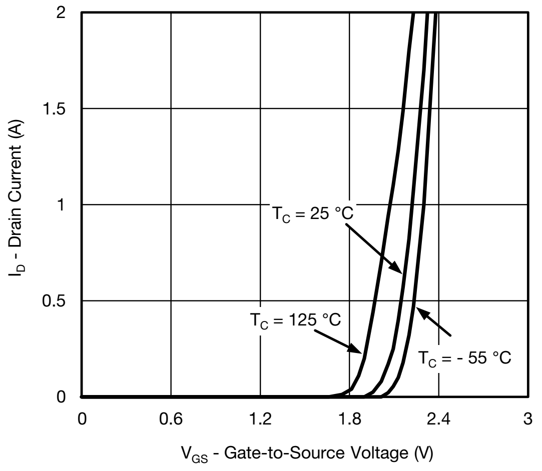
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

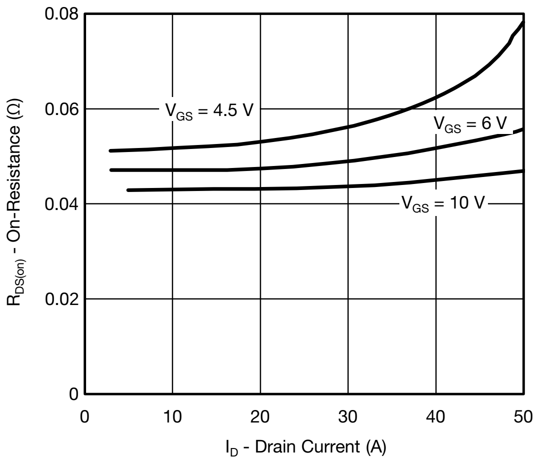
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



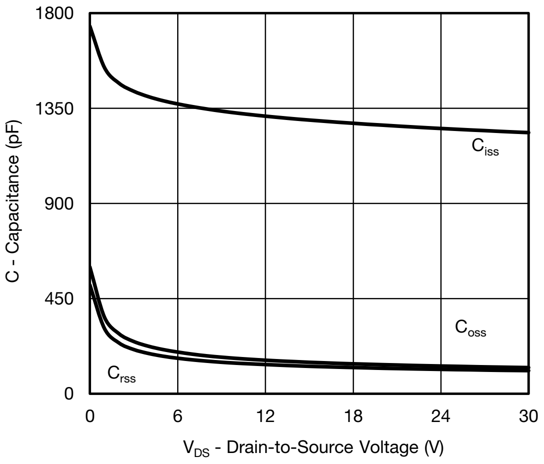
Output Characteristics



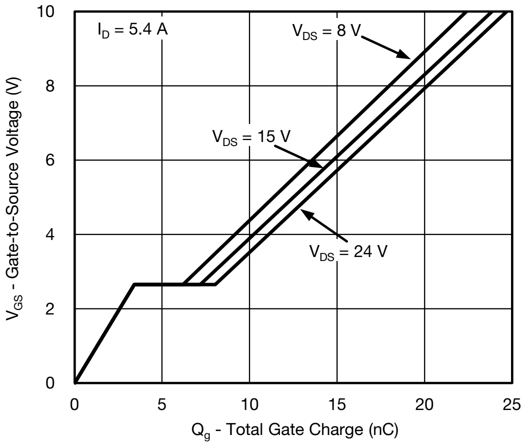
Transfer Characteristics



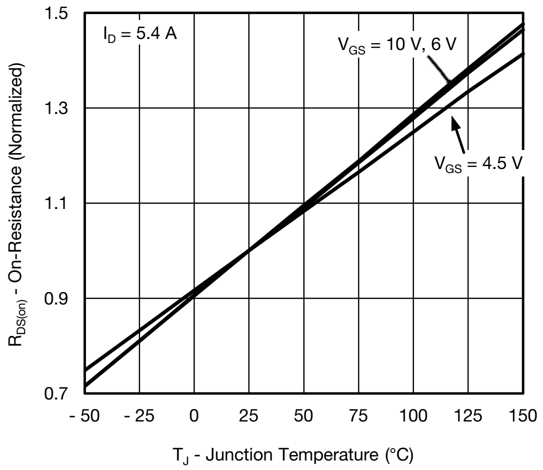
On-Resistance vs. Drain Current



Capacitance

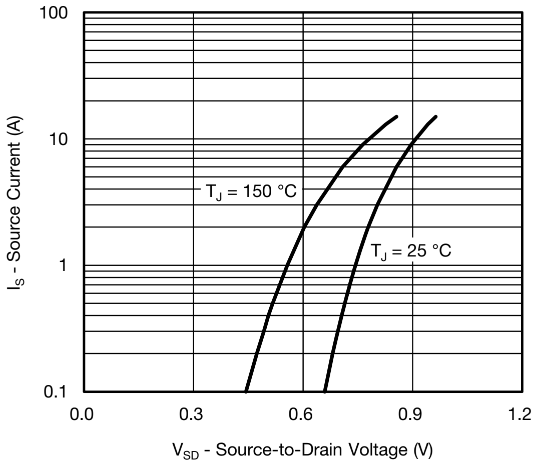


Gate Charge

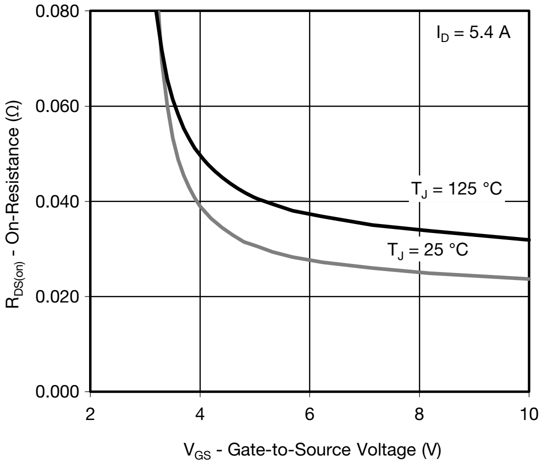


On-Resistance vs. Junction Temperature

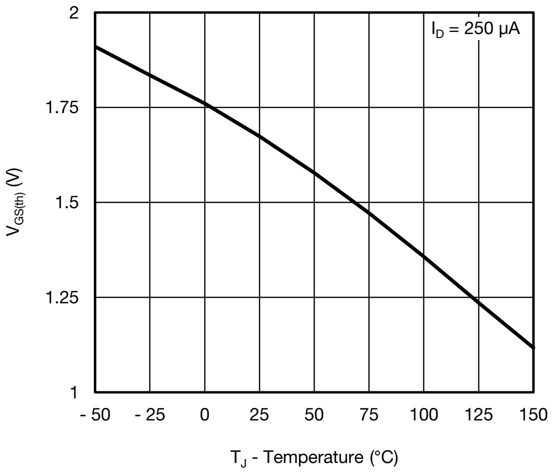
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



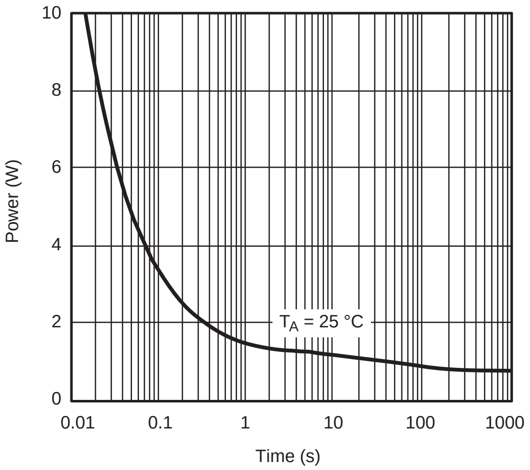
Source-Drain Diode Forward Voltage



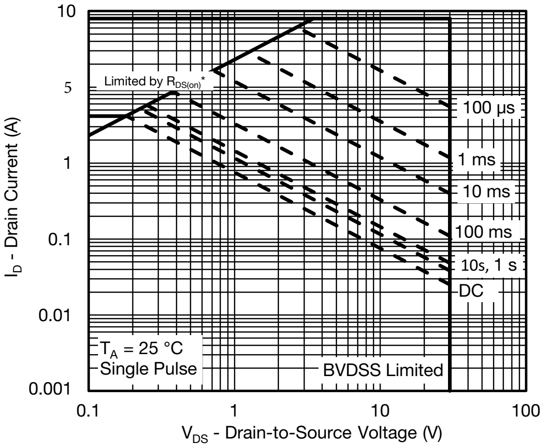
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



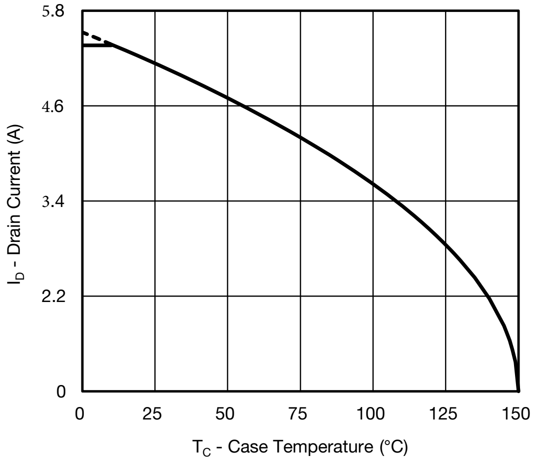
Single Pulse Power (Junction-to-Ambient)



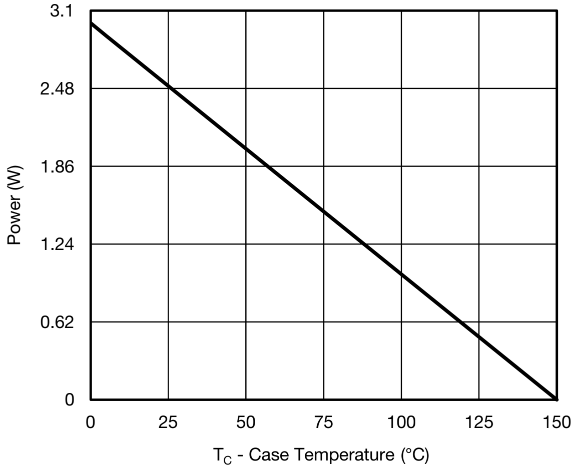
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

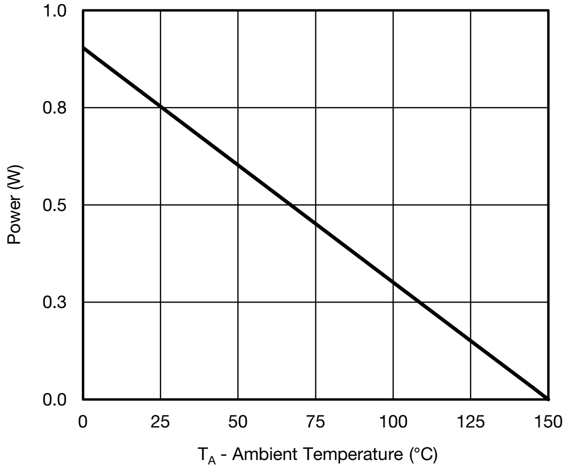
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



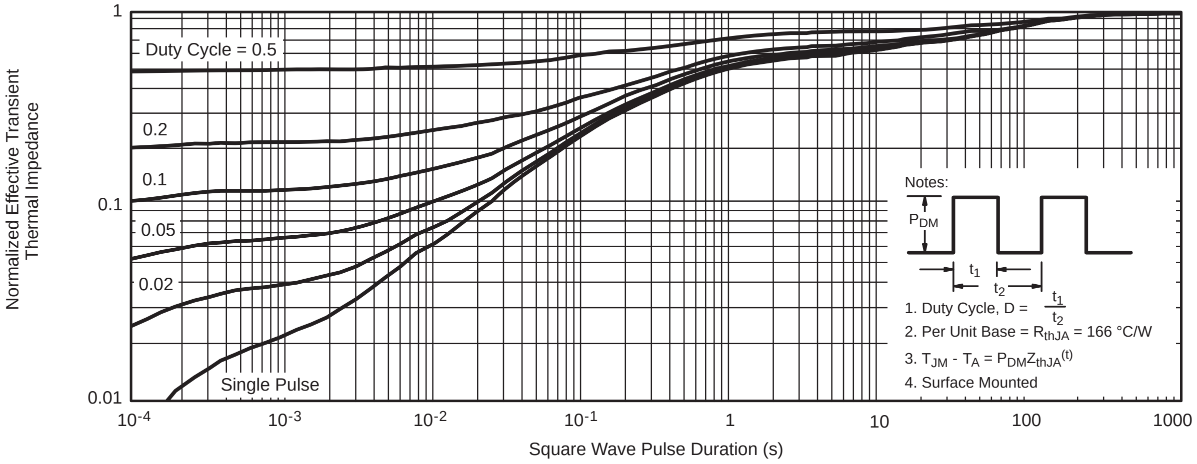
Power, Junction-to-Foot



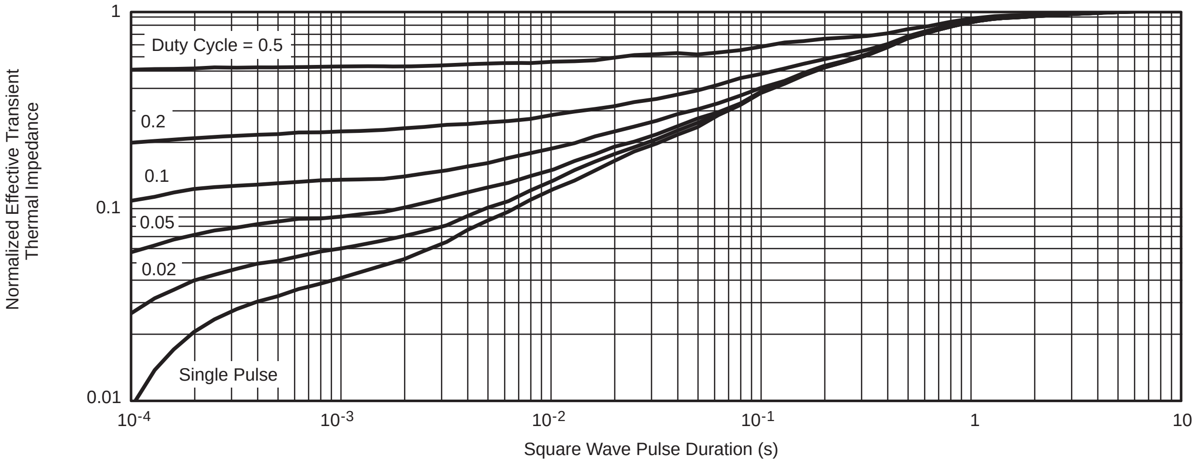
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

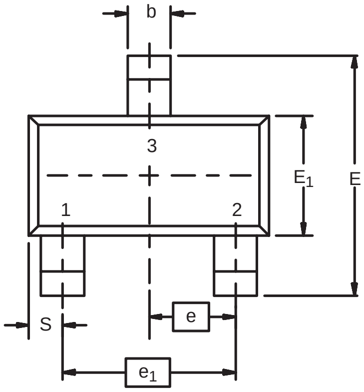


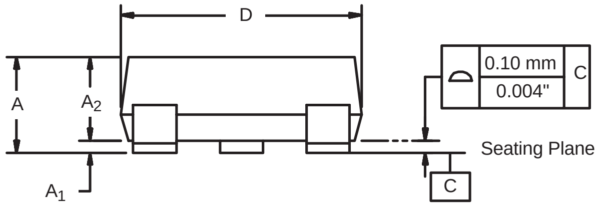
Normalized Thermal Transient Impedance, Junction-to-Ambient

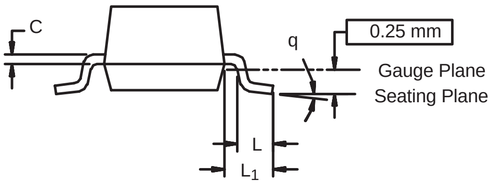


Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-23 (TO-236): 3-LEAD







Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

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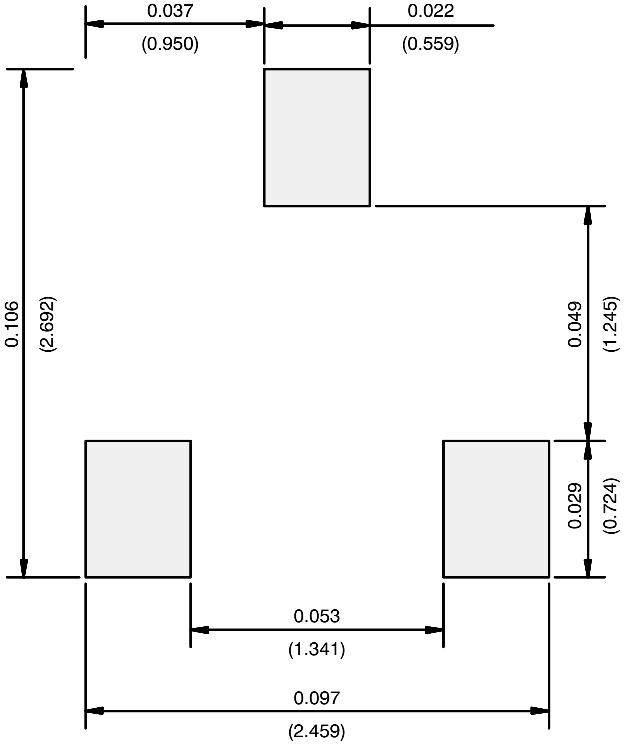
DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)